

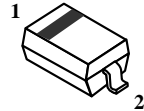
Surface Mount Schottky Barrier Diode

 Lead(Pb)-Free

Features:

- * High Breakdown Voltage.
- * Low Turn-on Voltage.
- * Gurad Ring Construction for Transient Protection.

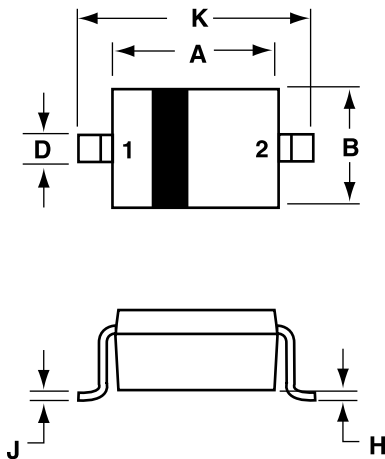
SCHOTTKY DIODE
100 VOLTS
75m AMPERES



SOD-123

SOD-123 Outline Dimensions

Unit:mm



SOD-123		
Dim	Min	Max
A	2.55	2.85
B	1.40	1.80
C	0.95	1.35
D	0.50	0.70
E	0.30 REF	
H	-	0.10
J	-	0.15
K	3.55	3.85

PIN 1. CATHODE
 2. ANODE

Maximum Ratings (T_A=25°C Unless otherwise noted)

Characteristic	Symbol	Value	Unit
DC Reverse Voltage	V _R	100	V
Average Rectifier Forward Current	I _O	75	mA
Forward Continuous Current ¹	I _F	150	mA
Repetitive Peak Forward Current ¹ t _p < 1.0s, Duty Cycle < 50%	I _{FRM}	350	mA
Forward Surge Forward Current ¹ t _p = 10ms	I _{FSM}	750	mA
Power Dissipation	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	500	°C/W
Operation Junction Temperature Range	T _J	125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C

Electrical Characteristics (T_A=25°C Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Forward Voltage t _p <300S, duty Cycle<2% I _F =0.1mA I _F =10mA I _F =250mA	V _F	-	-	0.25 0.45 1.0	V
Reverse Leakage t _p <300S, duty Cycle<2% V _R =1.5V V _R =1.5V, T _j =60°C V _R =1.0V V _R =1.0V, T _j =60°C V _R =50V V _R =50V, T _j =60°C V _R =75V V _R =75V, T _j =60°C	I _R	-	-	0.5 5.0 0.8 7.5 2.0 15 5.0 20	μA
Total Capacitance V _R =0V, f=1.0MHz V _R =1.0V, f=1.0MHz	C _J	-	10 6.0	-	pF

Note: 1. Valid Provided that terminals are kept at specified ambient temperature.

Electrical Characteristic curves($T_A=25^{\circ}\text{C}$)

